

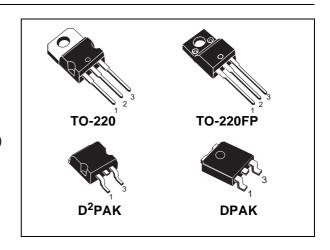
STGP3NB60F - STGD3NB60F

STGP3NB60FD-STGF3NB60FD-STGB3NB60FD

N-CHANNEL 3A - 600V - TO-220/TO-220FP/DPAK/D²PAK PowerMESH™ IGBT

TYPE	V _{CES}	V _{CE(sat)} (Typ) @125°C	I c @125°C
STGP3NB60F	600 V	< 2.4 V	3 A
STGD3NB60F	600 V	< 2.4 V	3 A
STGP3NB60FD	600 V	< 2.4 V	3 A
STGF3NB60FD	600 V	< 2.4 V	3 A
STGB3NB60FD	600 V	< 2.4 V	3 A

- HIGH INPUT IMPEDANCE (VOLTAGE DRIVEN)
- LOW ON-VOLTAGE DROP (V_{cesat})
- LOW GATE CHARGE
- HIGH CURRENT CAPABILITY
- OFF LOSSES INCLUDE TAIL CURRENT
- HIGH FREQUENCY OPERATION
- SHORT CIRCUIT RATED

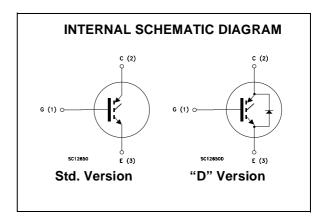


DESCRIPTION

Using the latest high voltage technology based on a patented strip layout, STMicroelectronics has designed an advanced family of IGBTs, the Power-MESH™ IGBTs, with outstanding performances. The suffix "F" identifies a family optimized to achieve very low switching times for frequency applications (<40 KHz)

APPLICATIONS

- MOTOR CONTROLS
- SMPS AND PFC IN BOTH HARD SWITCHING AND RESONANT TOPOLOGIES



ORDERING INFORMATION

	_		
SALES TYPE	MARKING	PACKAGE	PACKAGING
STGP3NB60F	GP3NB60F	TO-220	TUBE
STGD3NB60FT4	GD3NB60F	DPAK	TAPE & REEL
STGP3NB60FD	GP3NB60FD	TO-220	TUBE
STGF3NB60FD	GF3NB60FD	TO-220FP	TUBE
STGB3NB60FDT4	GB3NB60FD	D ² PAK	TAPE & REEL

June 2003 1/14

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Value		
		TO-220/D ² PAK	TO-220FP	DPAK	
V _{CES}	Collector-Emitter Voltage (V _{GS} = 0)		600		V
V _{ECR}	Emitter-Collector Voltage		20		V
V _{GE}	Gate-Emitter Voltage		±20		V
Ic	Collector Current (continuous) at T _C = 25°C		6		Α
Ic	Collector Current (continuous) at T _C = 100°C		3		
I _{CM} (■)	Collector Current (pulsed)		24		Α
I _f (1)	Forward Current		3		Α
I _{fm} (1)	Forward Current Pulsed		24		Α
P _{TOT}	Total Dissipation at T _C = 25°C	68	25	60	W
	Derating Factor	0.55	0.2	0.47	W/°C
V _{ISO}	Insulation Withstand Voltage A.C.	2500		V	
T _{stg}	Storage Temperature	– 55 to 150			°C
Tj	Max. Operating Junction Temperature		150		

^(■) Pulse width limited by safe operating area

THERMAL DATA

		TO-220/D ² PAK	TO-220FP	DPAK	
Rthj-case	Thermal Resistance Junction-case Max	1.8	5	2.1	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	62.	5	100	°C/W
Rthc-h	Thermal Resistance Case-heatsink Typ	0.5		°C/W	

ELECTRICAL CHARACTERISTICS ($T_{CASE} = 25^{\circ}C$ UNLESS OTHERWISE SPECIFIED) MAIN PARAMETERS

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
V _{BR(CES)}	Collector-Emitter Breakdown Voltage	$I_C = 250 \mu A, V_{GE} = 0$	600			V
I _{CES}	Collector cut-off (V _{GE} = 0)	V _{CE} = Max Rating, T _C = 25°C V _{CE} = Max Rating, T _C = 125°C			50 100	μA μA
I _{GES}	Gate-Emitter Leakage Current (V _{CE} = 0)	$V_{GE} = \pm 20V$, $V_{CE} = 0$			±100	nA
V _{GE(th)}	Gate Threshold Voltage	$V_{CE} = V_{GE}, I_{C} = 250 \mu\text{A}$	3		5	V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	V _{GE} = 15 V, I _C = 3 A V _{GE} = 15 V, I _C = 3 A, Tj =125°C		1.9 1.6	2.4	V V

⁽¹⁾ For "D" version only

SWITCHING PARAMETERS

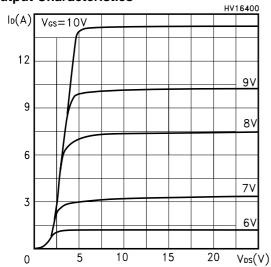
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
9fs	Forward Transconductance	V _{CE} = 25 V, Ic = 3 A		2		S
C _{ies} C _{oes} C _{res}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V _{CE} = 25 V, f = 1 MHz, V _{GE} = 0		230 33 6		pF pF pF
$egin{array}{c} Q_g \ Q_{ge} \ Q_{gc} \end{array}$	Total Gate Charge Gate-Emitter Charge Gate-Collector Charge	V _{CE} = 480 V, I _C = 3 A, V _{GE} = 15 V		16 1.5 8	20	nC nC nC
t _{d(on)}	Turn-on Delay Time Rise Time	V _{CC} = 480 V, I _C = 3 A R _G = 10Ω, V _{GE} = 15 V		12.5 4		ns ns
(di/dt) _{on} Eon	Turn-on Current Slope Turn-on Switching Losses	V_{CC} = 480 V, I_{C} = 3 A R _G =10 Ω V _{GE} = 15 V,Tj = 125°C		840 31		A/μs μJ
$\begin{array}{c} t_{\text{c}} \\ t_{\text{f}}(\text{V}_{\text{off}}) \\ t_{\text{d}}(\text{off}) \\ t_{\text{f}} \\ \text{E}_{\text{off}}(^{**}) \\ \text{Ets} \end{array}$	Cross-over Time Off Voltage Rise Time Delay Time Fall Time Turn-off Switching Loss Total Switching Loss	V_{CC} = 480 V, I_{C} = 3 A, R_{GE} = 10 Ω , V_{GE} = 15 V Tj = 25 °C		220 60 105 150 125 149		ns ns ns ns µJ µJ
$\begin{array}{c} t_{c} \\ t_{f}(V_{off}) \\ t_{d}(_{off}) \\ t_{f} \\ E_{off}(^{**}) \\ E_{ts} \end{array}$	Cross-over Time Off Voltage Rise Time Delay Time Fall Time Turn-off Switching Loss Total Switching Loss	$V_{cc} = 480 \text{ V, } I_{C} = 3 \text{ A,}$ $R_{GE} = 10 \Omega \text{ , } V_{GE} = 15 \text{ V}$ $Tj = 125 \text{ °C}$		490 174 230 305 295 326		ns ns ns ns µJ µJ

COLLECTOR-EMITTER DIODE ("D" VERSION)

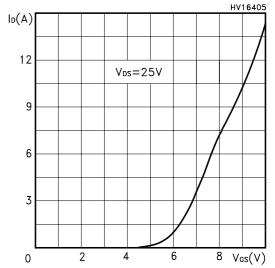
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
V _f	Forward On-Voltage	l _f = 1.5 A l _f = 1.5 A, Tj = 125 °C		1.31 0.95	1.8	V V
t _{rr} Q _{rr} I _{rrm}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_f = 3 \text{ A ,V}_R = 35 \text{ V,}$ $Tj = 125 ^{\circ}\text{C, di/dt} = 100 \text{ A/}\mu\text{s}$		45 70 2.7		ns nC A

Note: 1. Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %.
2. Pulse width limited by max. junction temperature.
(**)Losses include Also the Tail (Jedec Standardization)

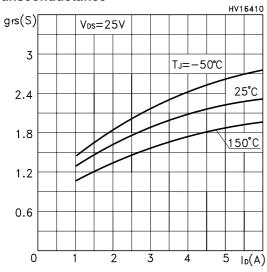
Output Characteristics



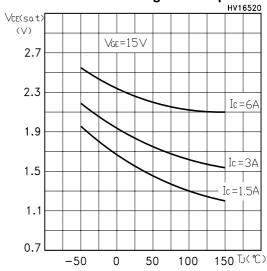
Transfer Characteristics



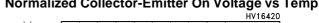
Transconductance

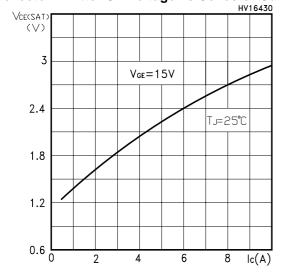


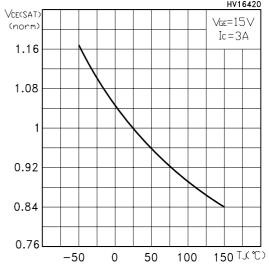
Collector-Emitter On Voltage vs Temperature



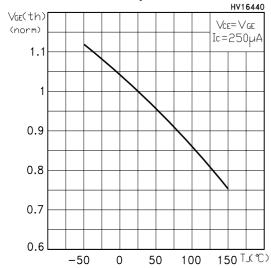
Collector-Emitter On Voltage vs Collector Current Normalized Collector-Emitter On Voltage vs Temp.

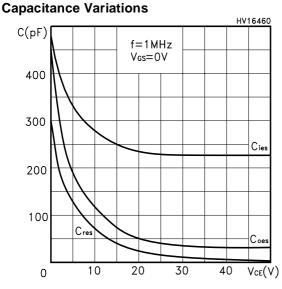




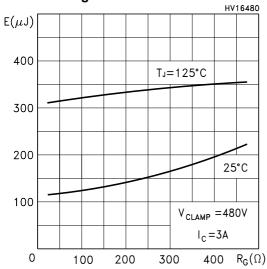


Gate Threshold vs Temperature

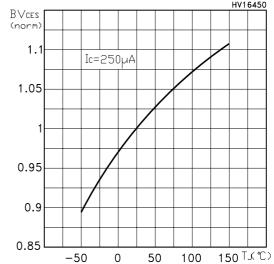




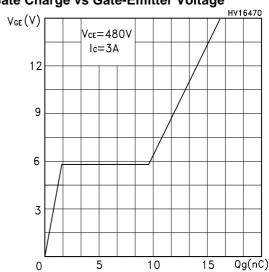
Total Switching Losses vs Gate Resistance



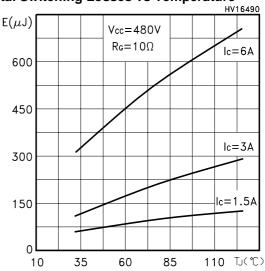
Normalized Breakdown Voltage vs Temperature



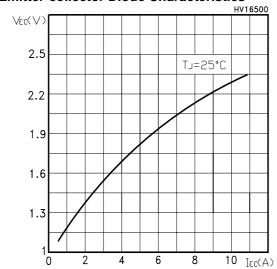
Gate Charge vs Gate-Emitter Voltage



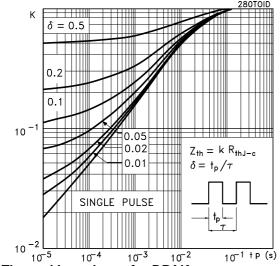
Total Switching Losses vs Temperature



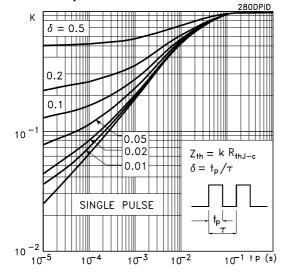
Emitter-collector Diode Characteristics



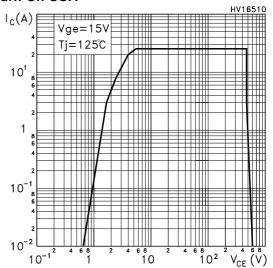
Thermal Impedance for TO-220 / D2PAK



Thermal Impedance for DPAK



Turn-Off SOA



Thermal Impedance for TO-220FP

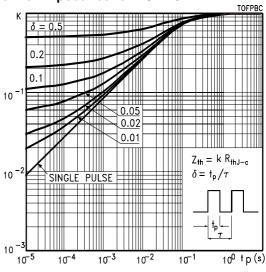


Fig. 1: Gate Charge test Circuit

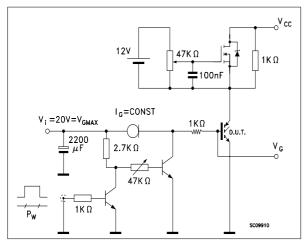
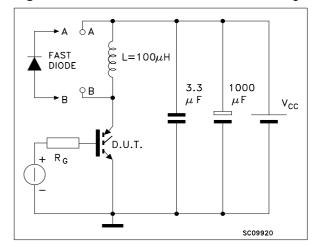
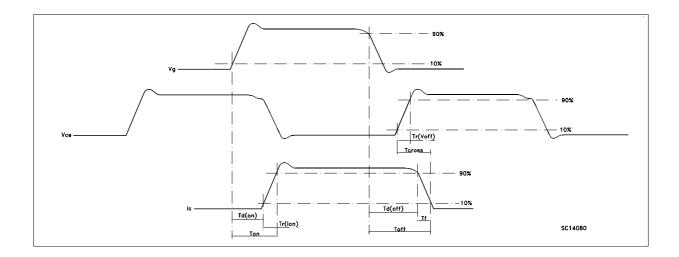


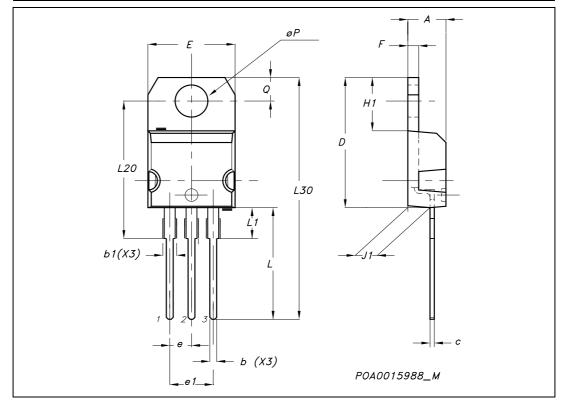
Fig. 2: Test Circuit For Inductive Load Switching





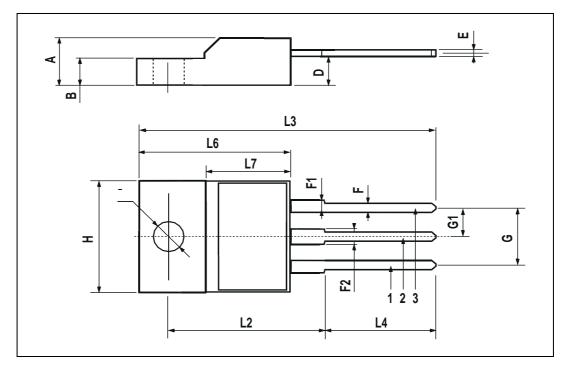
TO-220 MECHANICAL DATA

DIM		mm.			inch	
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
С	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
Е	10		10.40	0.393		0.409
е	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øΡ	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



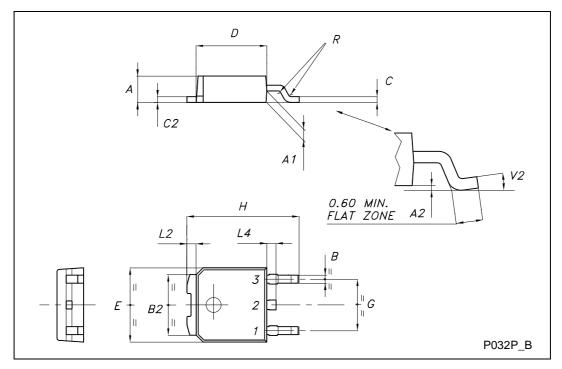
TO-220FP MECHANICAL DATA

DIM.		mm			inch	
DIIVI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
Α	4.4		4.6	0.173		0.181
В	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
Н	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	0.385		0.417
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



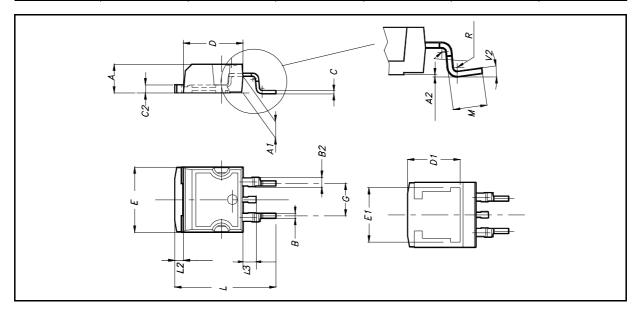
TO-252 (DPAK) MECHANICAL DATA

DIM.		mm inch				
DIWI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	2.20		2.40	0.087		0.094
A1	0.90		1.10	0.035		0.043
A2	0.03		0.23	0.001		0.009
В	0.64		0.90	0.025		0.035
B2	5.20		5.40	0.204		0.213
С	0.45		0.60	0.018		0.024
C2	0.48		0.60	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.60	0.252		0.260
G	4.40		4.60	0.173		0.181
Н	9.35		10.10	0.368		0.398
L2		0.8			0.031	
L4	0.60		1.00	0.024		0.039
V2	0°		8°	0°		0°

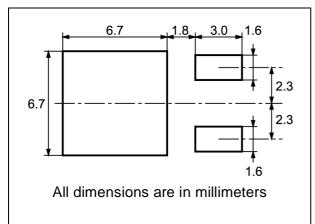


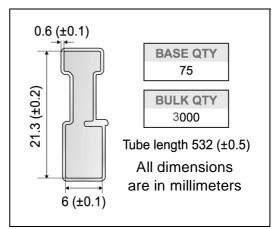
D²PAK MECHANICAL DATA

DIM		mm.			inch	
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
А	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
В	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
С	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	00		80			

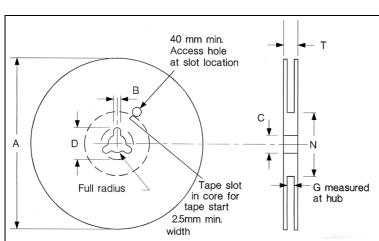


DPAK FOOTPRINT TUBE SHIPMENT (no suffix)*





TAPE AND REEL SHIPMENT (suffix "T4")*



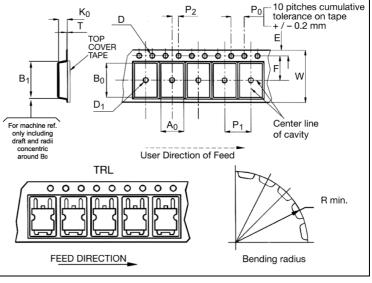
REEL MECHANICAL DATA

DIM.	mm		ine	ch
Dilli.	MIN.	MAX.	MIN.	MAX.
Α		330		12.992
В	1.5		0.059	
С	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	16.4	18.4	0.645	0.724
N	50		1.968	
Т		22.4		0.881

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	6.8	7	0.267	0.275
В0	10.4	10.6	0.409	0.417
B1		12.1		0.476
D	1.5	1.6	0.059	0.063
D1	1.5		0.059	
Е	1.65	1.85	0.065	0.073
F	7.4	7.6	0.291	0.299
K0	2.55	2.75	0.100	0.108
P0	3.9	4.1	0.153	0.161
P1	7.9	8.1	0.311	0.319
P2	1.9	2.1	0.075	0.082
R	40		1.574	
W	15.7	16.3	0.618	0.641

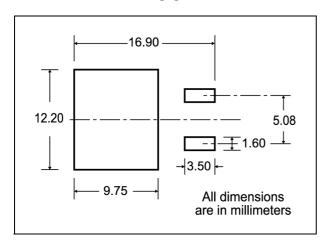
BASE QTY BULK QTY 2500 2500

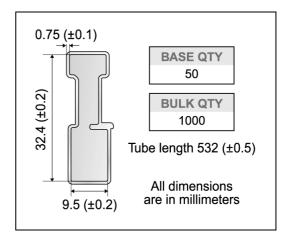


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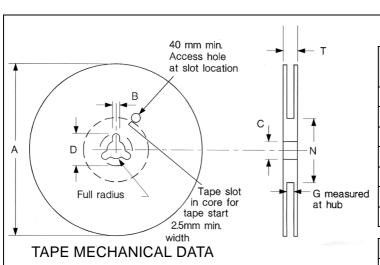
D²PAK FOOTPRINT

TUBE SHIPMENT (no suffix)*





TAPE AND REEL SHIPMENT (suffix "T4")*

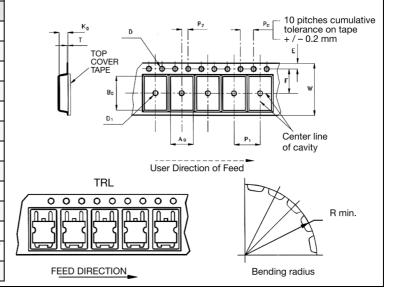


REEL MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
Α		330		12.992
В	1.5		0.059	
С	12.8	13.2	0.504	0.520
D	20.2		0795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

DIM.	mm		inch		
	MIN.	MAX.	MIN.	MAX.	
A0	10.5	10.7	0.413	0.421	
В0	15.7	15.9	0.618	0.626	
D	1.5	1.6	0.059	0.063	
D1	1.59	1.61	0.062	0.063	
E	1.65	1.85	0.065	0.073	
F	11.4	11.6	0.449	0.456	
K0	4.8	5.0	0.189	0.197	
P0	3.9	4.1	0.153	0.161	
P1	11.9	12.1	0.468	0.476	
P2	1.9	2.1	0.075	0.082	
R	50		1.574		
Т	0.25	0.35	0.0098	0.0137	
W	23.7	24.3	0.933	0.956	



* on sales

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